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<https://www.mouser.fr/ProductDetail/IXYS/IXTH11P50?qs=t7yjd2JO%2FgRLBgyOLKbAdg%3D%3D>

### IXTH11P50

Images are for reference only  
See Product Specifications


**Mouser No:** 747-IXTH11P50


**Mfr. No:** IXTH11P50

**Mfr.:** IXYS

**Customer No:**

**Description:** MOSFET -11 Amps -500V 0.75 Rds

**Datasheet:**  [IXTH11P50 Datasheet \(PDF\)](#)

**ECAD Model:**  PCB Symbol, Footprint & 3D Model


Download the free Library Loader to convert this file for your ECAD Tool. Learn more about the ECAD Model.

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**In Stock: 427**

**Stock:** 427 Can Dispatch Immediately



**On Order:** 420 Expected 6/1/2022

**Factory Lead Time:** 29 Weeks 

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**Pricing (EUR)**

| Qty.  | Unit Price | Ext. Price |
|-------|------------|------------|
| 1     | 9,94 €     | 9,94 €     |
| 10    | 9,57 €     | 95,70 €    |
| 120   | 8,92 €     | 1 070,40 € |
| 510   | 7,76 €     | 3 957,60 € |
| 1 020 | 5,69 €     | 5 803,80 € |

| Specifications  |   |                                     |
|--|---|-------------------------------------|
| Product Attribute  | Attribute Value   | Search Similar                      |
| <b>Manufacturer:</b>   | IXYS  | <input type="checkbox"/>            |
| <b>Product Category:</b>   | MOSFET  | <input checked="" type="checkbox"/> |
| <b>RoHS:</b>   |  Details |                                     |
| <b>Technology:</b>   | Si  | <input type="checkbox"/>            |
| <b>Mounting Style:</b>   | Through Hole  | <input type="checkbox"/>            |
| <b>Package/Case:</b>   | TO-247-3  | <input type="checkbox"/>            |
| <b>Transistor Polarity:</b>  | P-Channel   | <input type="checkbox"/>            |


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**IXYS**



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**LSIC1MO170E0750 N-Channel SiC MOSFET**

750mΩ N-channel MOSFET optimized for high-voltage, high-frequency, and high-efficiency applications.  
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|   |                       |                          |
|---|-----------------------|--------------------------|
| Number of Channels:                     | 1 Channel             | <input type="checkbox"/> |
| Vds - Drain-Source Breakdown Voltage:   | 500 V                 | <input type="checkbox"/> |
| Id - Continuous Drain Current:          | 11 A                  | <input type="checkbox"/> |
| Rds On - Drain-Source Resistance:       | 750 mOhms             | <input type="checkbox"/> |
| Vgs - Gate-Source Voltage:              | - 20 V, + 20 V        | <input type="checkbox"/> |
| Vgs th - Gate-Source Threshold Voltage: | 5 V                   | <input type="checkbox"/> |
| Qg - Gate Charge:                       | 130 nC                | <input type="checkbox"/> |
| Minimum Operating Temperature:          | - 55 C                | <input type="checkbox"/> |
| Maximum Operating Temperature:          | + 150 C               | <input type="checkbox"/> |
| Pd - Power Dissipation:                 | 300 W                 | <input type="checkbox"/> |
| Channel Mode:                           | Enhancement           | <input type="checkbox"/> |
| Packaging:                              | Tube                  | <input type="checkbox"/> |
| Brand:                                  | IXYS                  |                          |
| Configuration:                          | Single                |                          |
| Fall Time:                              | 35 ns                 |                          |
| Forward Transconductance - Min:         | 5 S                   |                          |
| Height:                                 | 21.46 mm              |                          |
| Length:                                 | 16.26 mm              |                          |
| Product Type:                           | MOSFET                |                          |
| Rise Time:                              | 27 ns                 |                          |
| Series:                                 | IXTH11P50             |                          |
| Factory Pack Quantity:                  | 30                    |                          |
| Subcategory:                            | MOSFETs               |                          |
| Transistor Type:                        | 1 P-Channel           |                          |
| Type:                                   | Standard Power MOSFET |                          |
| Typical Turn-Off Delay Time:            | 35 ns                 |                          |
| Typical Turn-On Delay Time:             | 33 ns                 |                          |
| Width:                                  | 5.3 mm                |                          |
| Unit Weight:                            | 6 g                   |                          |

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1200V drain-source voltage rating, 25mΩ to 160mΩ resistance range, and 14A to 70A currents.  
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